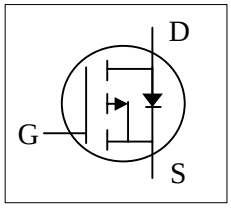
AP9451GG

RoHS-compliant Product

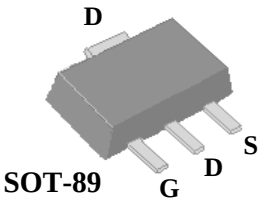
Advanced Power Electronics Corp.

P-CHANNEL ENHANCEMENT MODE POWER MOSFET

- **Simple Drive Requirement**
- **Small Package Outline**
- **Capable of 2.5V Gate Drive**
- **RoHS Compliant**



BV_{DSS}	-20V
$R_{DS(ON)}$	135mΩ
I_D	- 2.3A



SOT-89

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current[3]	-2.3	A
I_D@T_A=70℃	Continuous Drain Current[3]	-1.9	A
I_{DM}	Pulsed Drain Current[1]	-12	A
P_D@T_A=25℃	Total Power Dissipation	1.25	W
	Linear Derating Factor	0.01	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	100	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-20	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=-1mA	-	-0.02	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V, I_D=-2.3A	-	-	135	mΩ
		V_{GS}=-2.5V, I_D=-1.0A	-	-	240	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-0.5	-	-1.5	V
g_{fs}	Forward Transconductance	V_{DS}=-5V, I_D=-2.3A	-	2.3	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V, V_{GS}=0V	-	-	-1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=-16V, V_{GS}=0V	-	-	-25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D= -2.3A	-	5.5	9	nC
Q_{gs}	Gate-Source Charge	V_{DS}= -15V	-	1	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}= -4.5V	-	2.5	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=-10V	-	9	-	ns
t_r	Rise Time	I_D=-1A	-	25	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=-5V	-	20	-	ns
t_f	Fall Time	R_D=10Ω	-	10	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	270	430	pF
C_{oss}	Output Capacitance	V_{DS}= -20V	-	100	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	35	-	pF
R_g	Gate Resistance	f=1.0MHz	-	8	12	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	T_j=25℃, I_S=-1A, V_{GS}=0V	-	-	-1.6	V
t_{rr}	Reverse Recovery Time[2]	I_S= -2.5A, V_{GS}=0V,	-	27	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	27	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mount on FR4 board, t ≦ 10s.

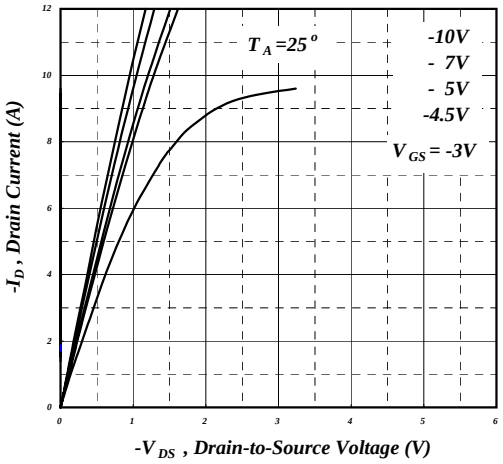


Fig 1. Typical Output Characteristics

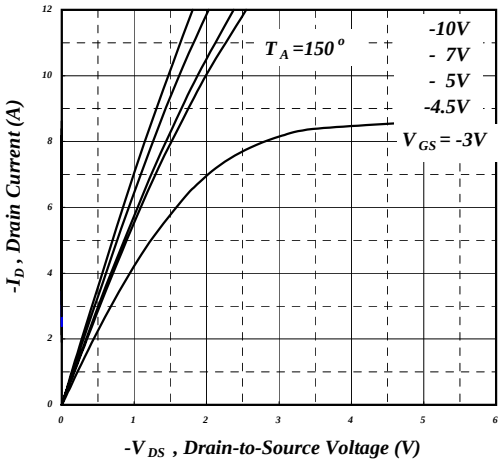


Fig 2. Typical Output Characteristics

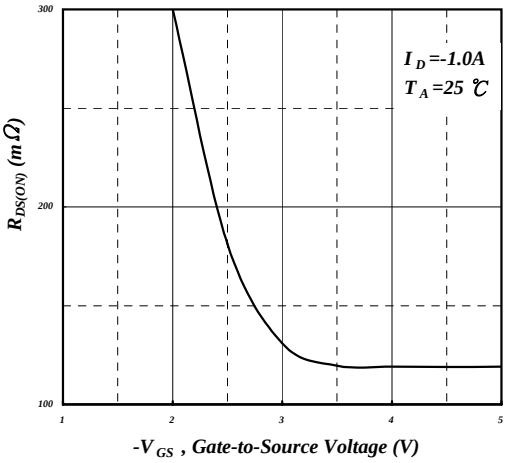


Fig 3. On-Resistance v.s. Gate Voltage

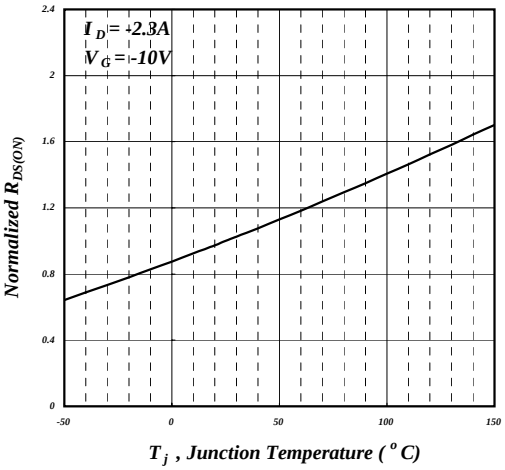


Fig 4. Normalized On-Resistance

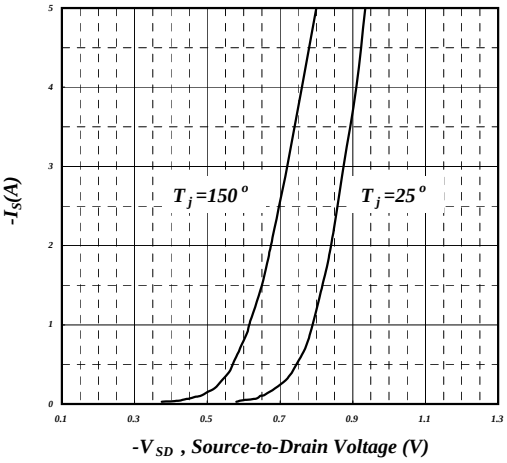


Fig 5. Forward Characteristic of Reverse Diode

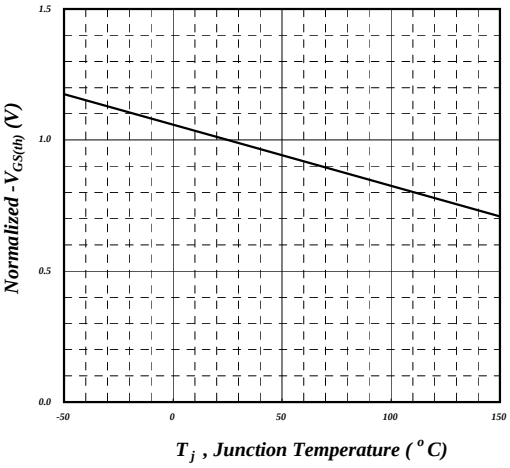


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

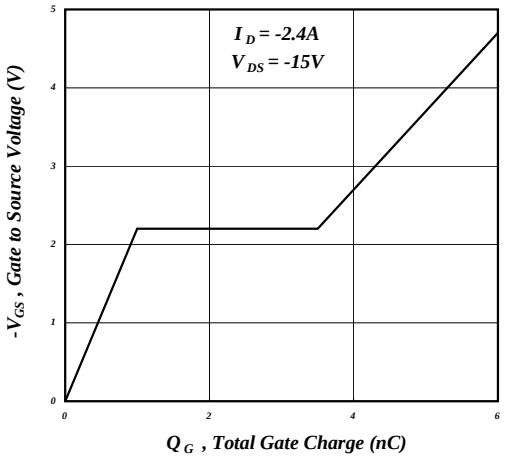


Fig 7. Gate Charge Characteristics

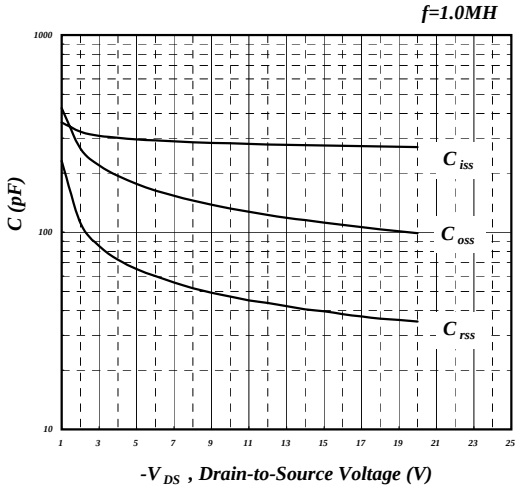


Fig 8. Typical Capacitance Characteristics

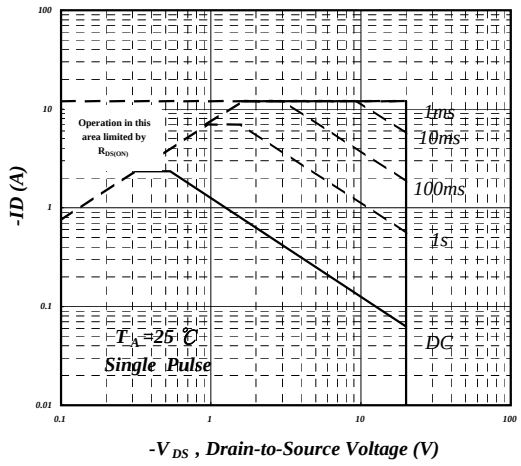


Fig 9. Maximum Safe Operating Area

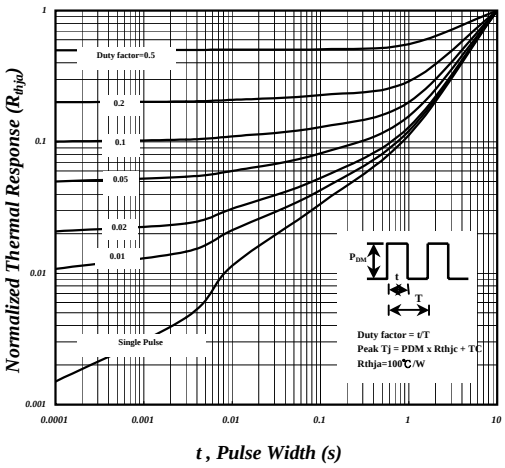


Fig 10. Effective Transient Thermal Impedance

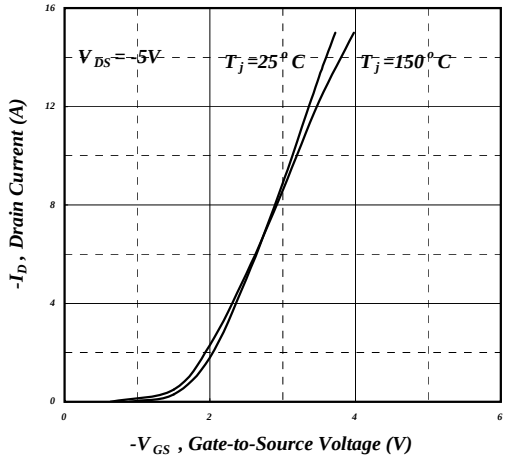


Fig 11. Transfer Characteristics

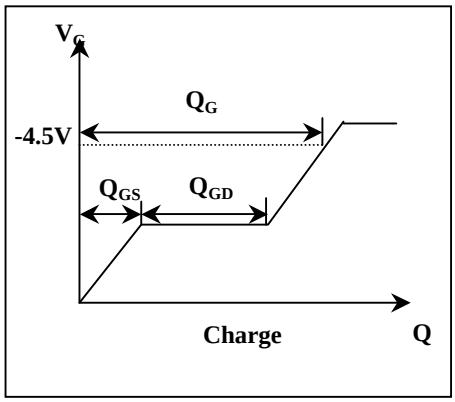


Fig 12. Gate Charge Waveform